



Fig.2

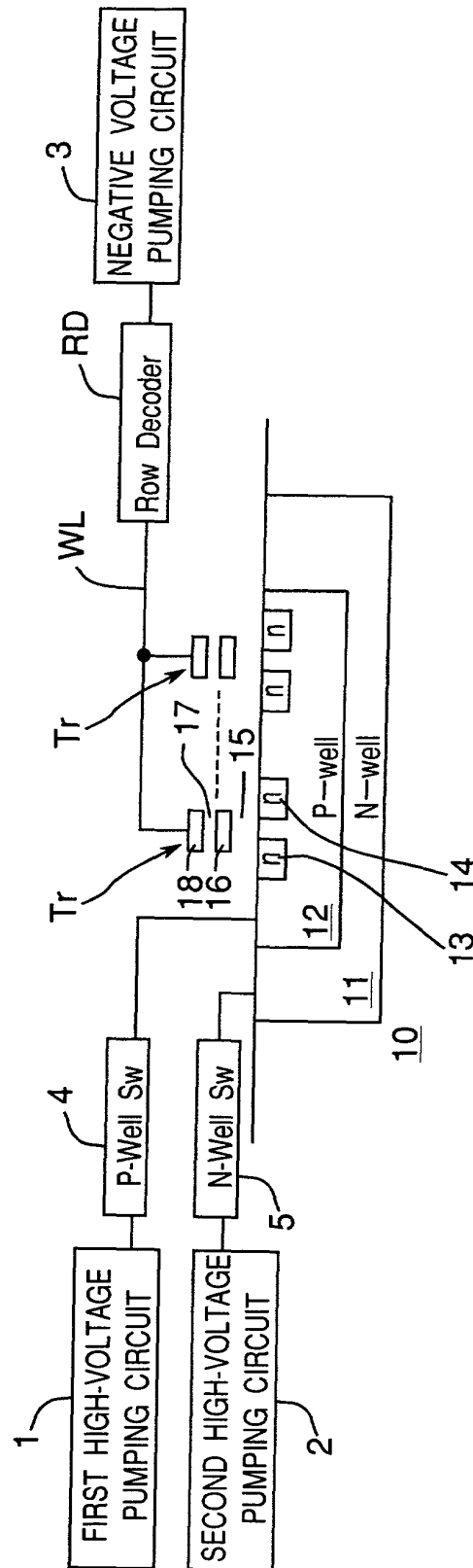


Fig.3

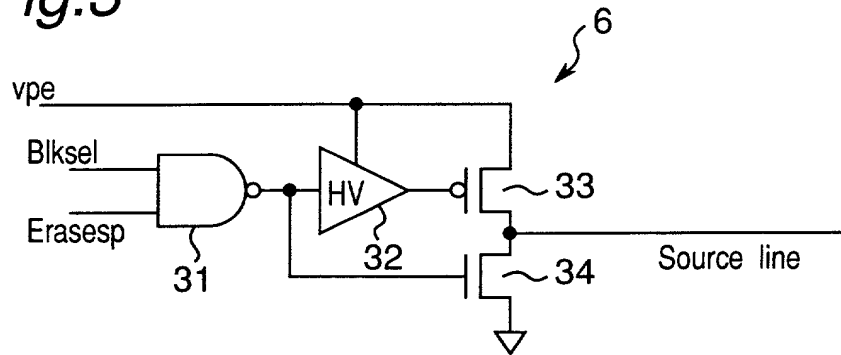


Fig.4

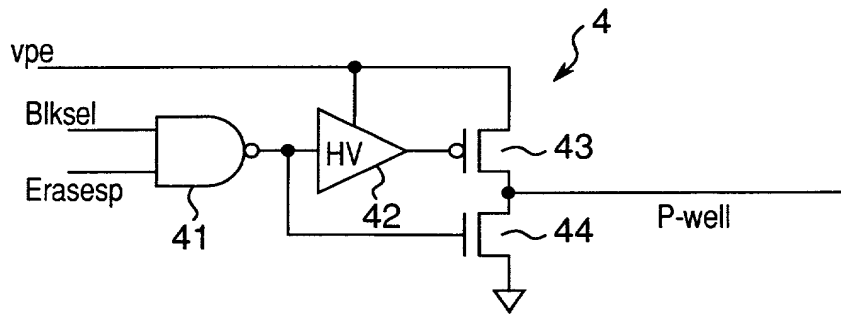
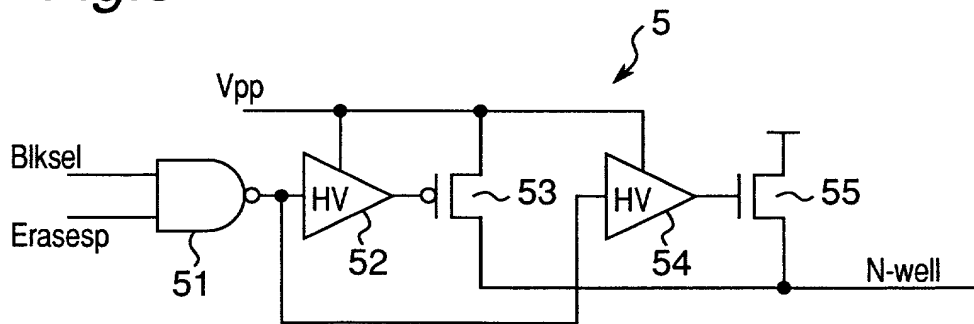
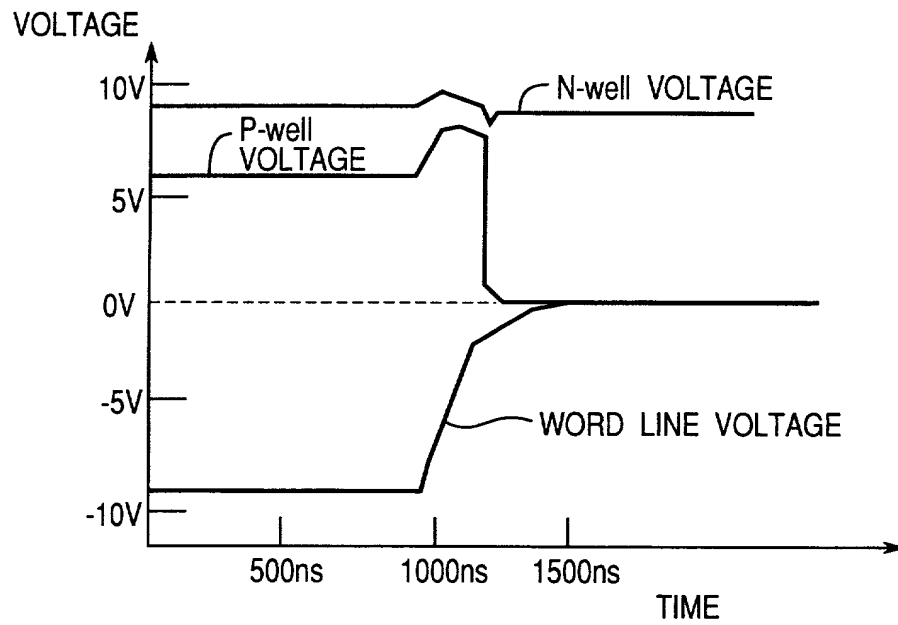


Fig.5



*Fig.6*



The diagram illustrates a semiconductor device structure. A substrate 10 contains a P-well 11 and an N-well 12. A gate stack 13 is formed on the surface, with a gate electrode 14. A row decoder 3 is connected to a word line WL. A P-well switch 4 is connected to the P-well 11, and an N-well switch 5 is connected to the N-well 12. A high-voltage pumping circuit 71 is connected to the P-well switch 4, and an auxiliary pumping circuit 72 is connected to the N-well switch 5. A negative voltage pumping circuit 3 is connected to the row decoder 3. Transistors Tr are shown at the intersections of the word line WL and the gate stack 13. A dashed line 15 indicates a boundary between two regions of the device. Other labels include 16, 17, 18, and 19.

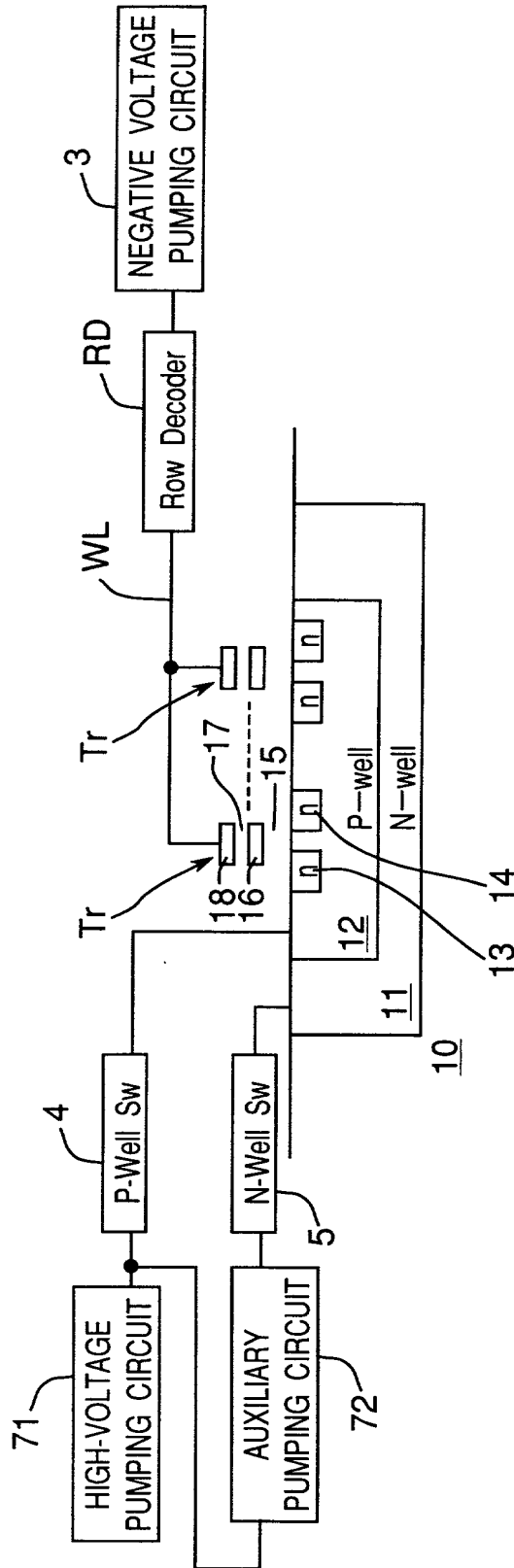


Fig.8

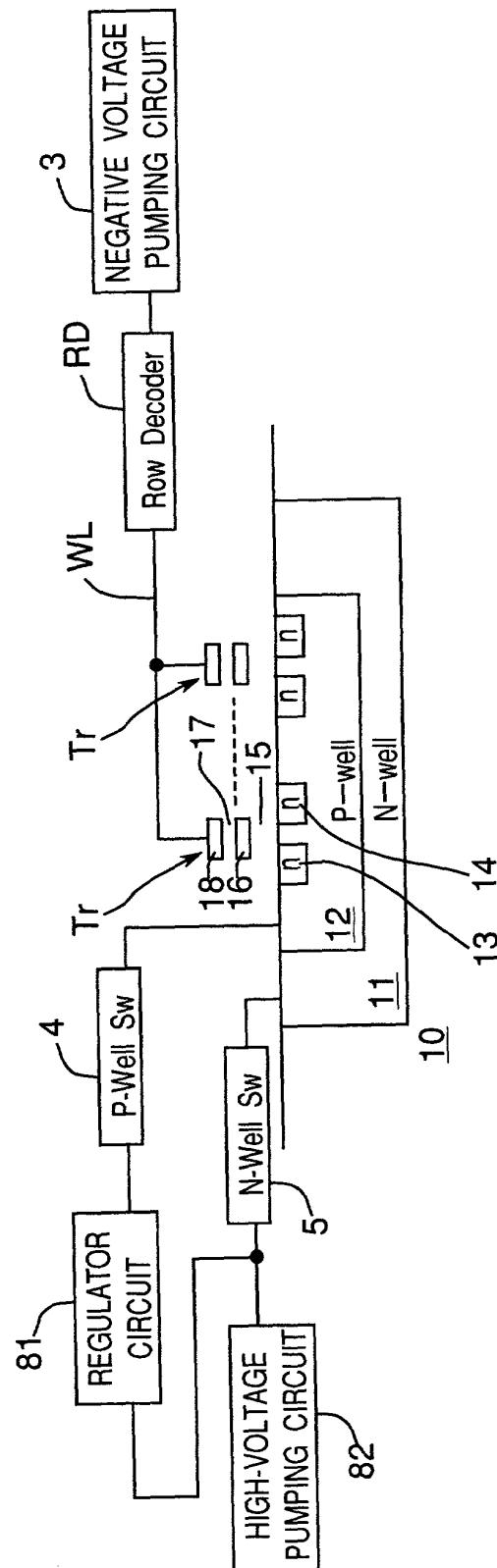


Fig.9

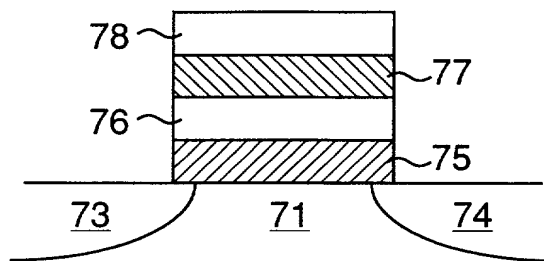


Fig.10

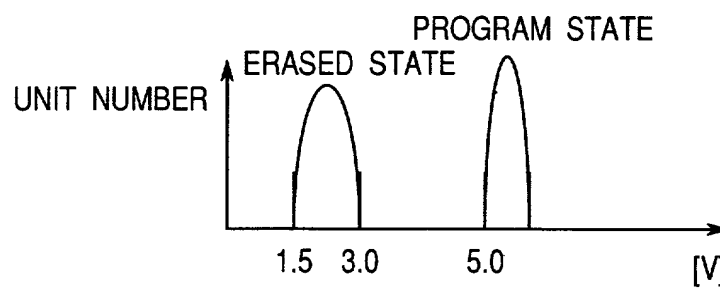


Fig.11

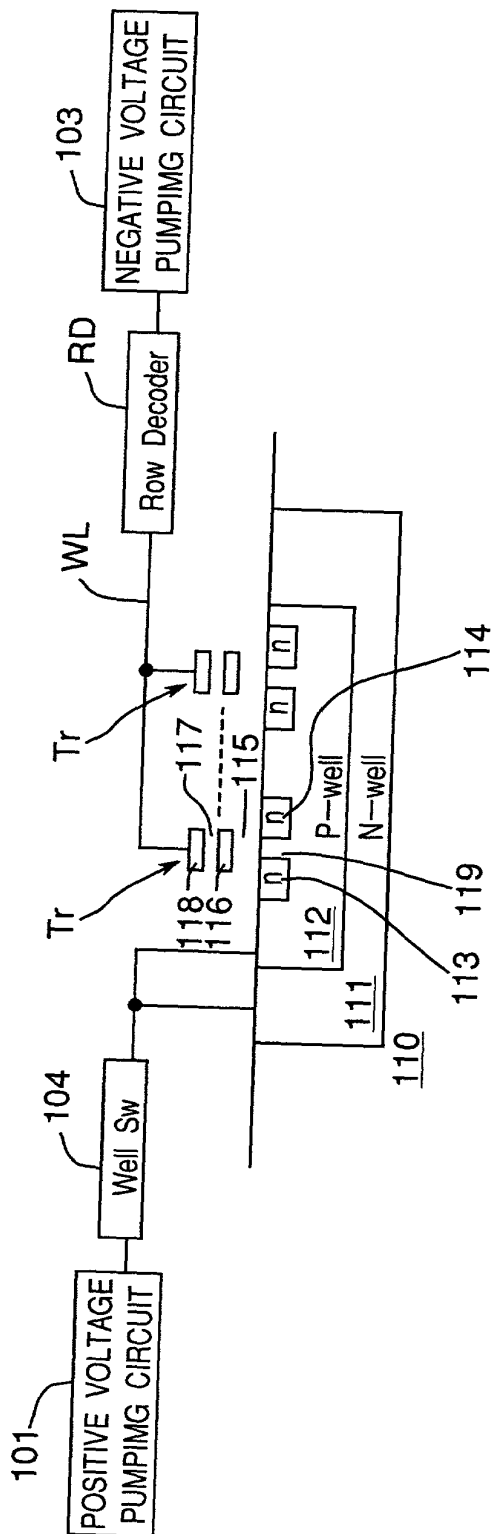




Fig. 12

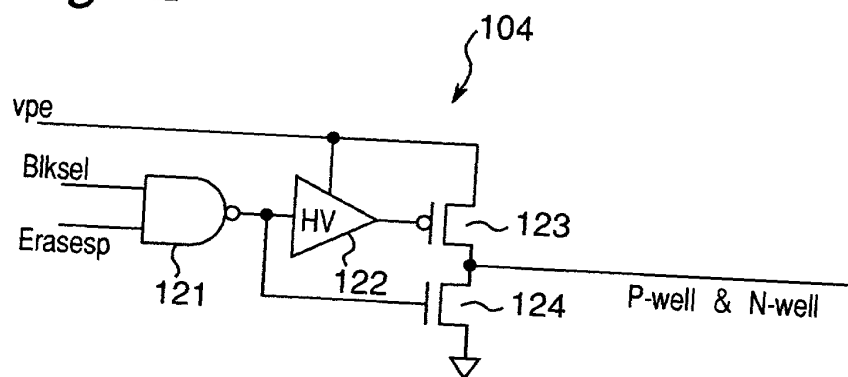


Fig.13

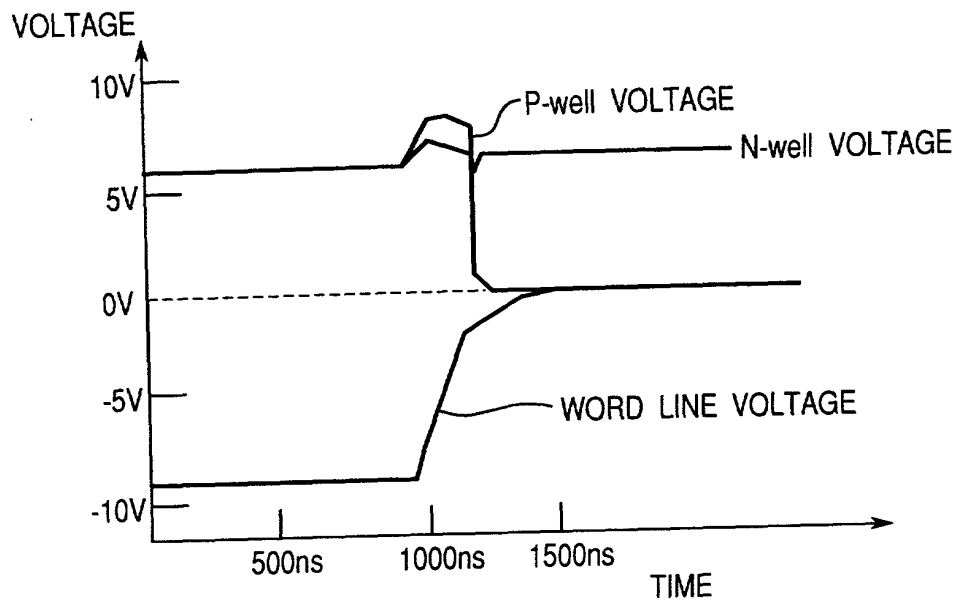


Fig.14

